

FIG. 1

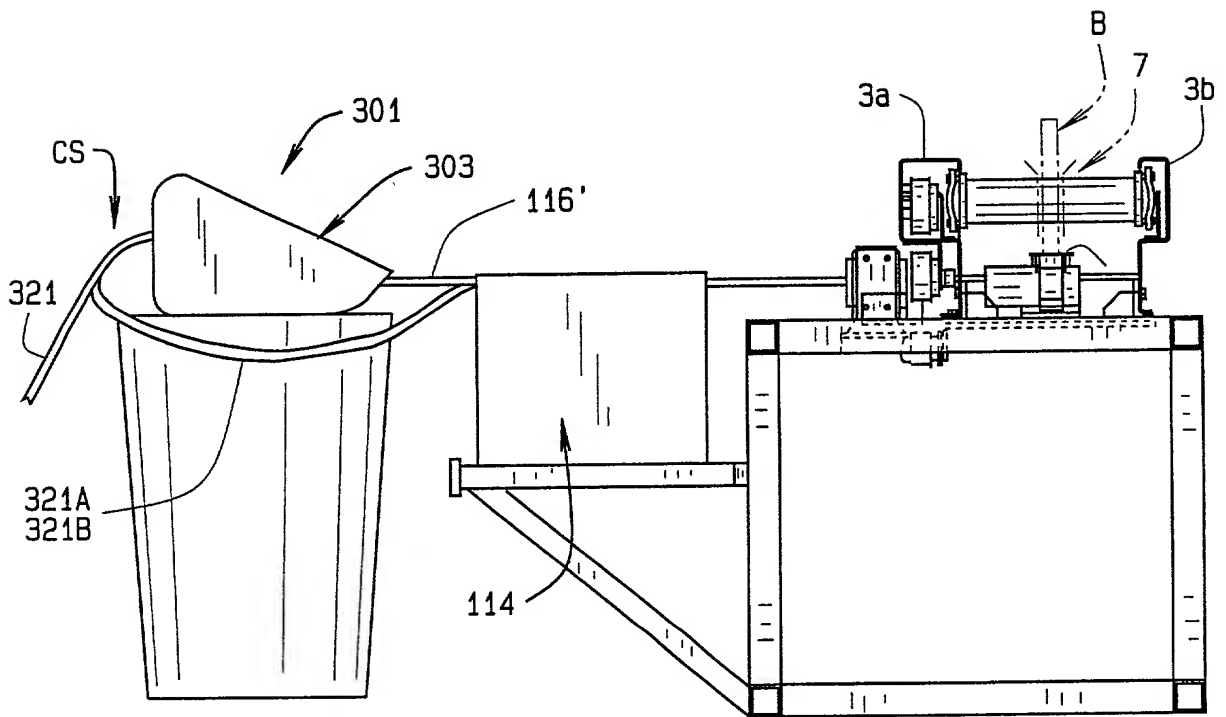


FIG. 27

FIG. 2

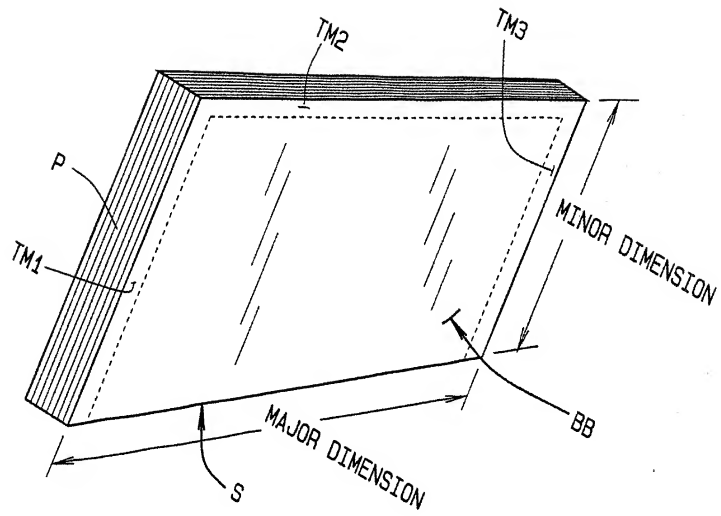


FIG. 2

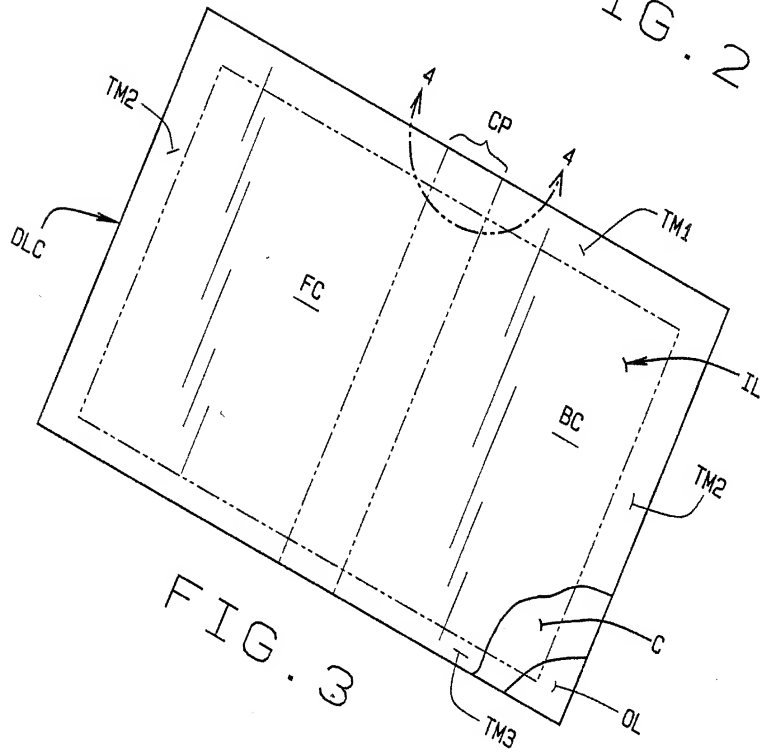
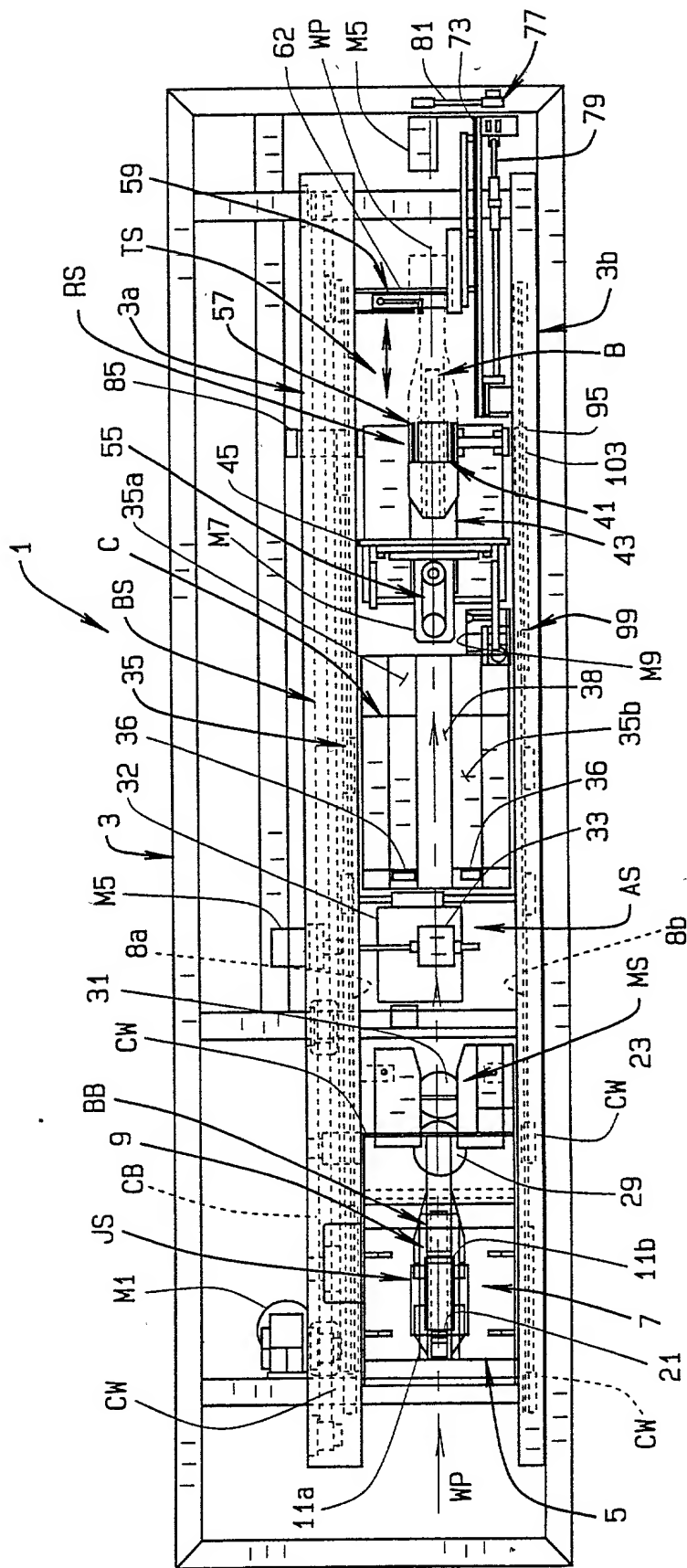


FIG. 3

A cross-sectional view of a semiconductor device. The device consists of a substrate with a bottom layer labeled OL. On top of the substrate is a layer with a series of peaks. The peaks are labeled LP, CP, SL, IL, and C. A DLC layer is shown on the left side of the peaks. A bracket groups the peaks under the label CP.

FIG. 4A



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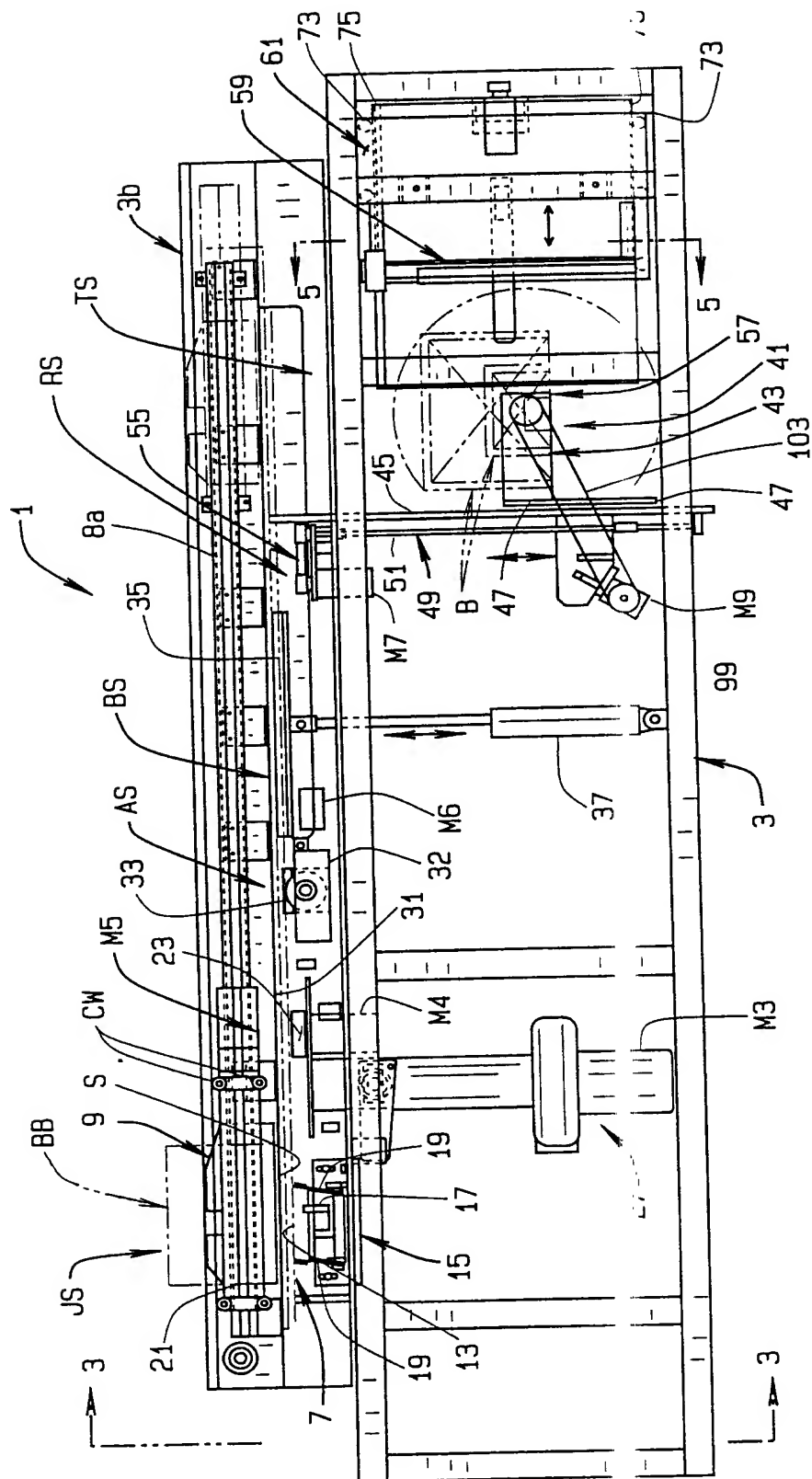


FIG. 6

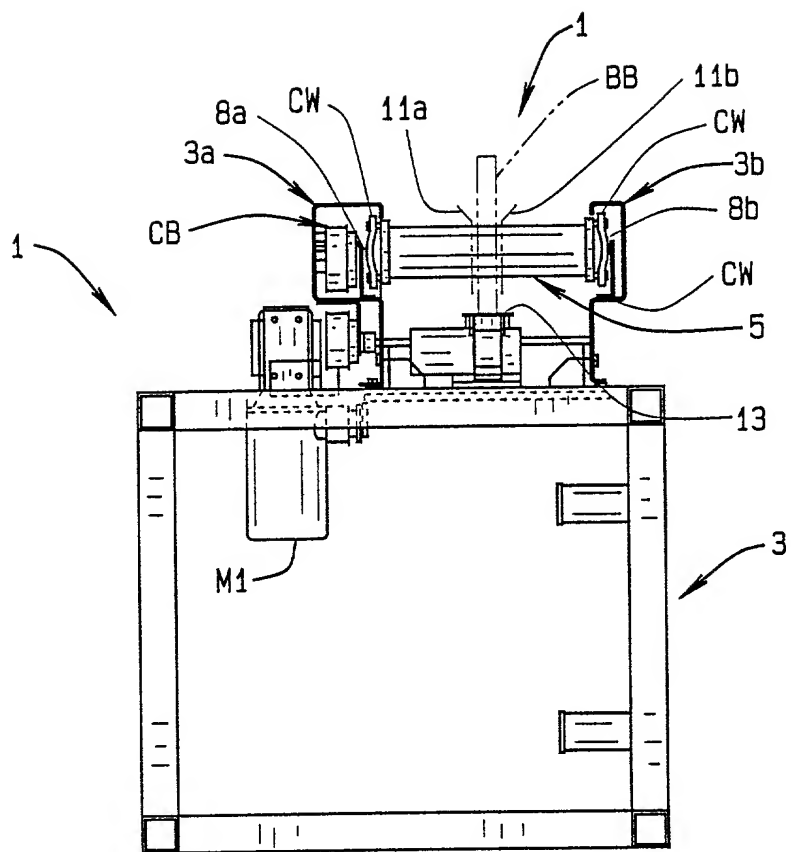
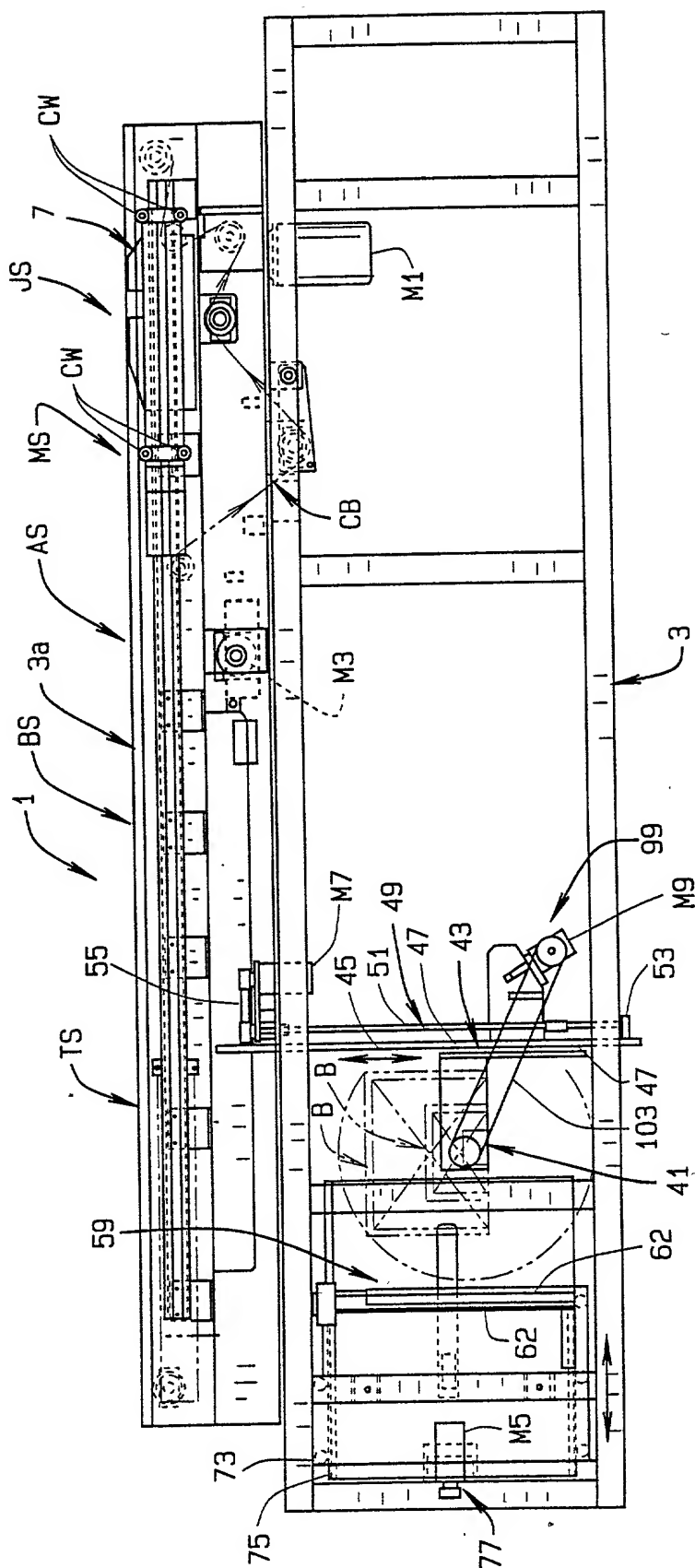


FIG. 7

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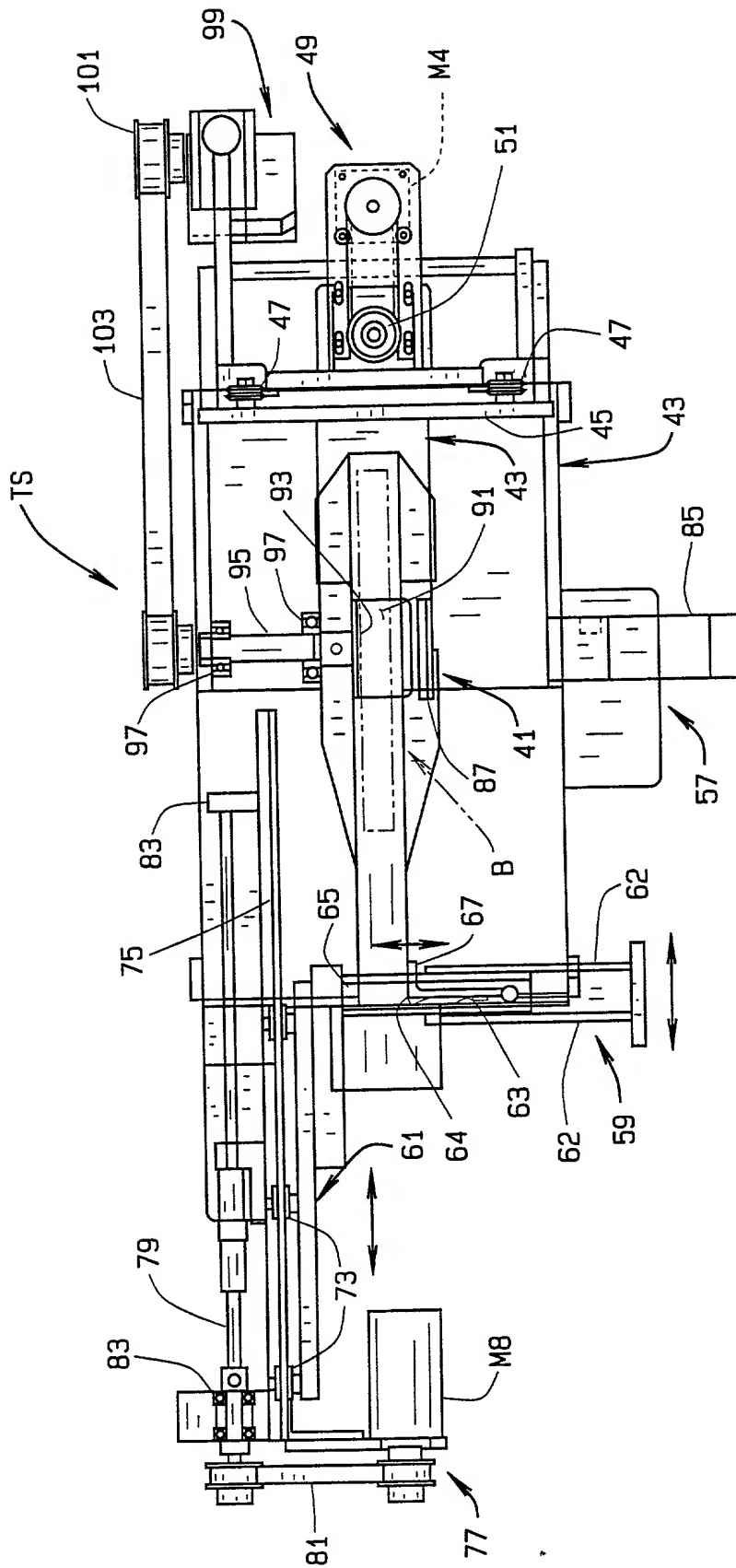


FIG. 11

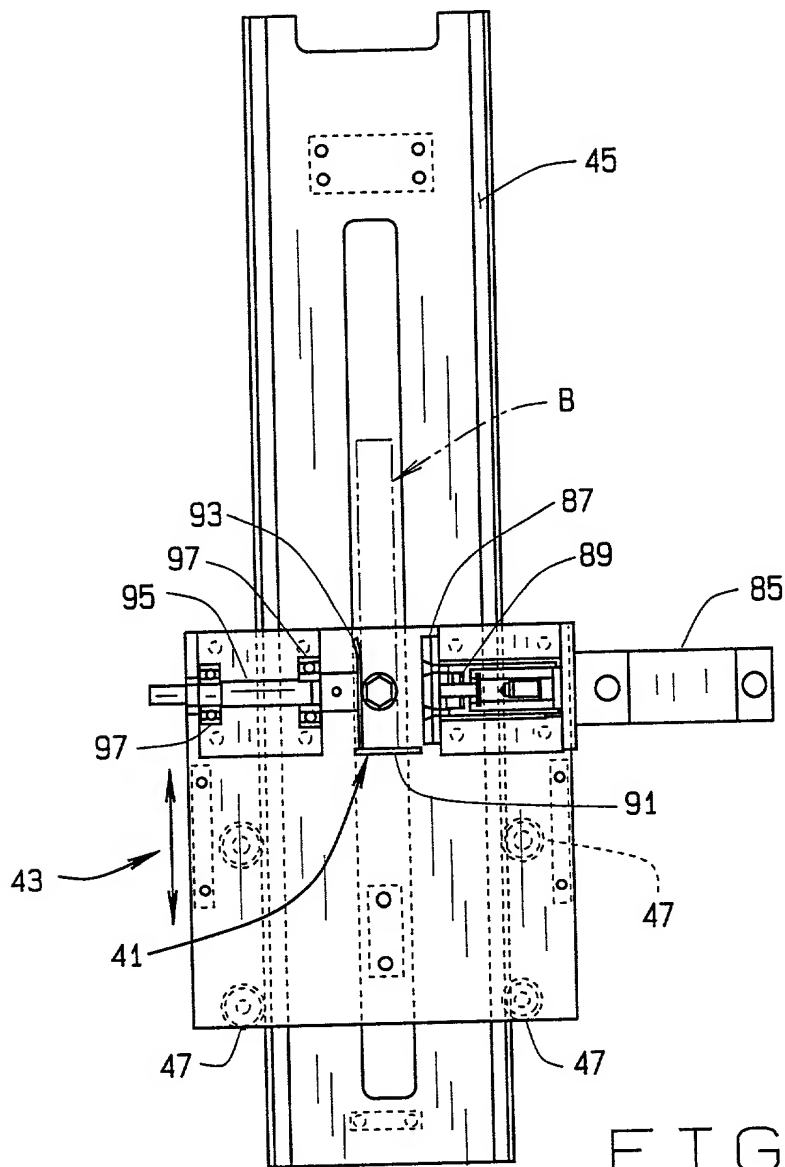


FIG. 12

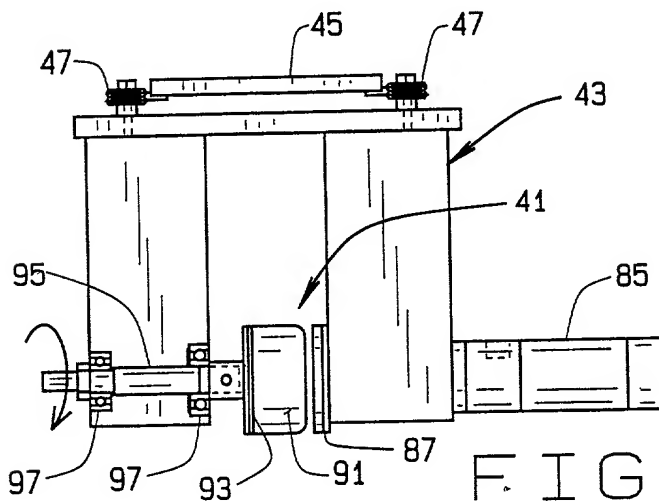
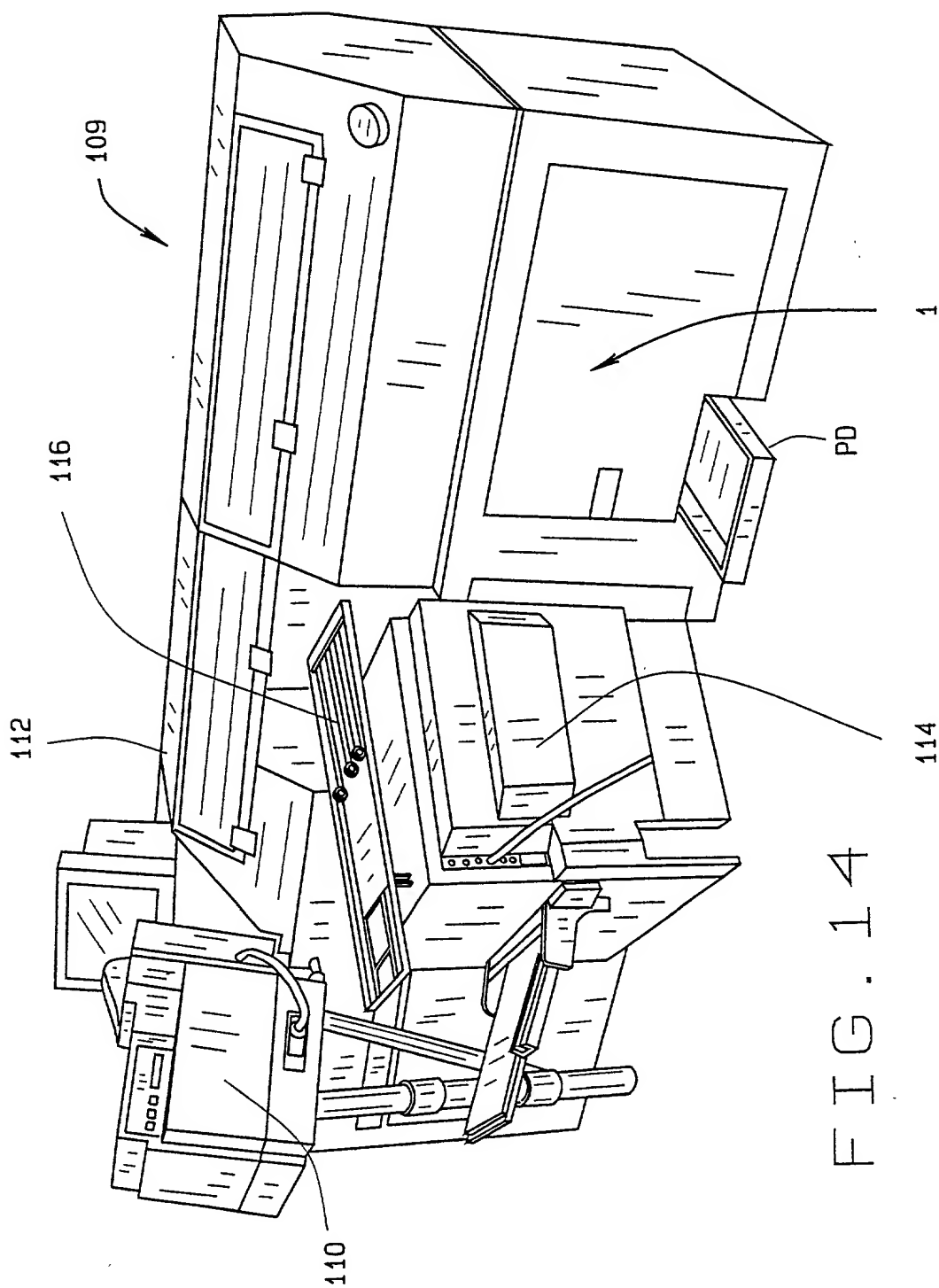
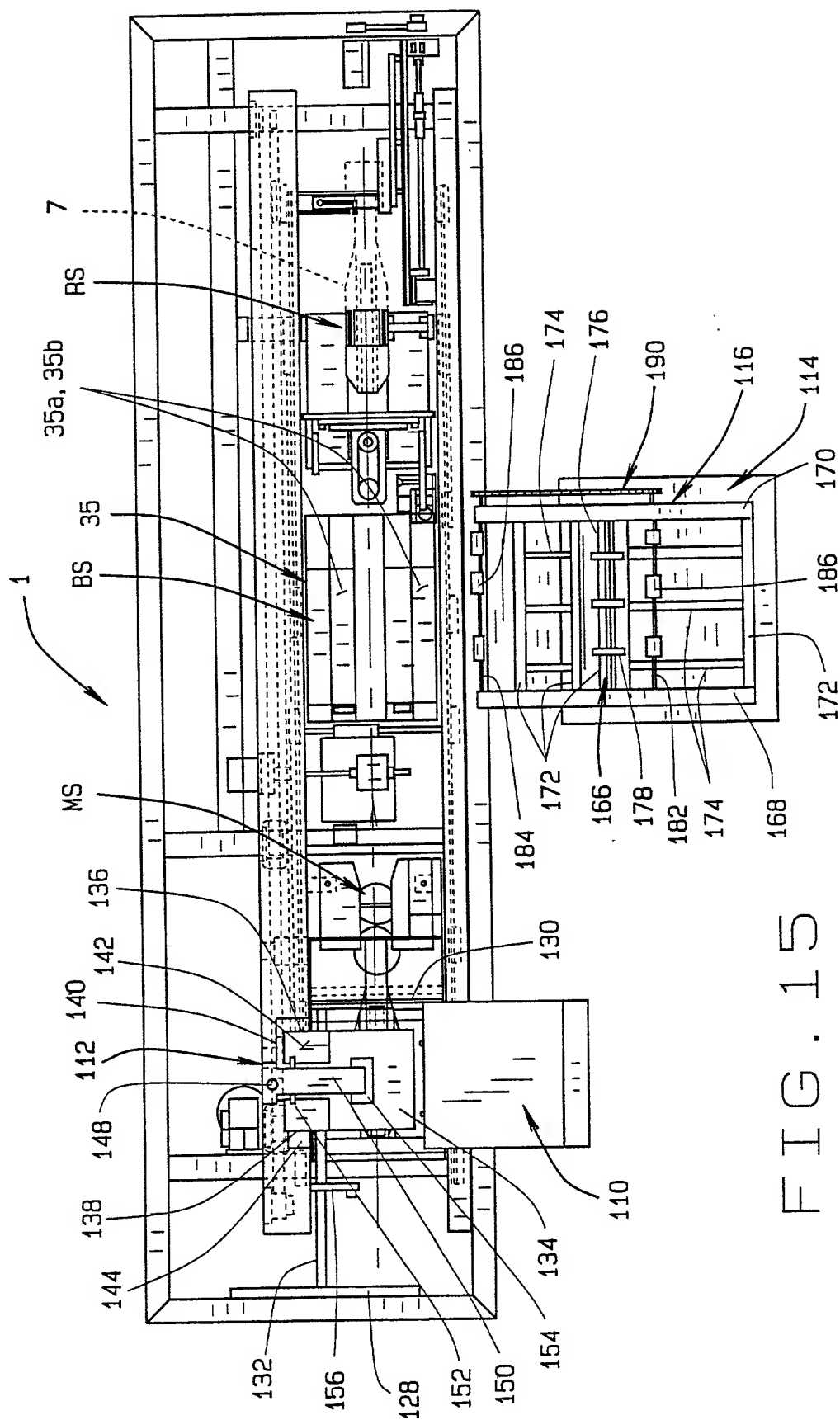


FIG. 13

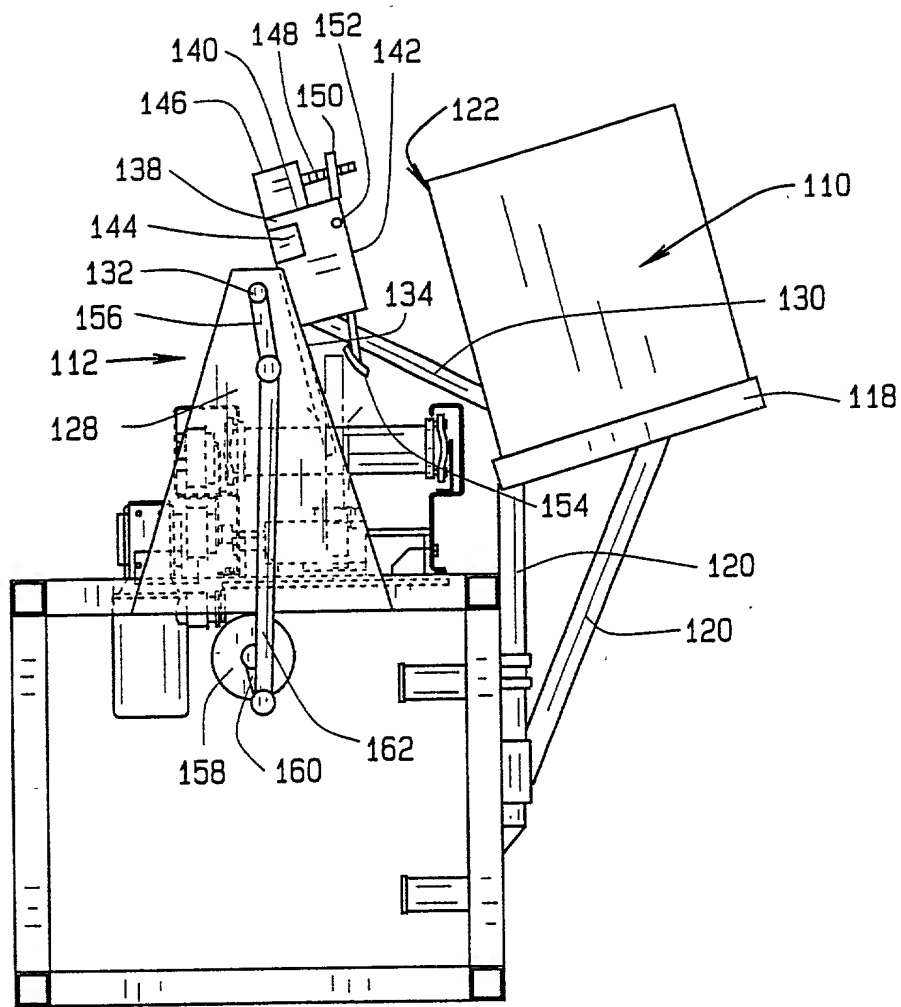


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FIG. 17



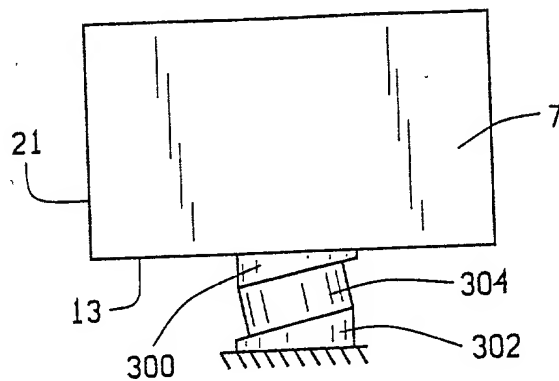


FIG. 19

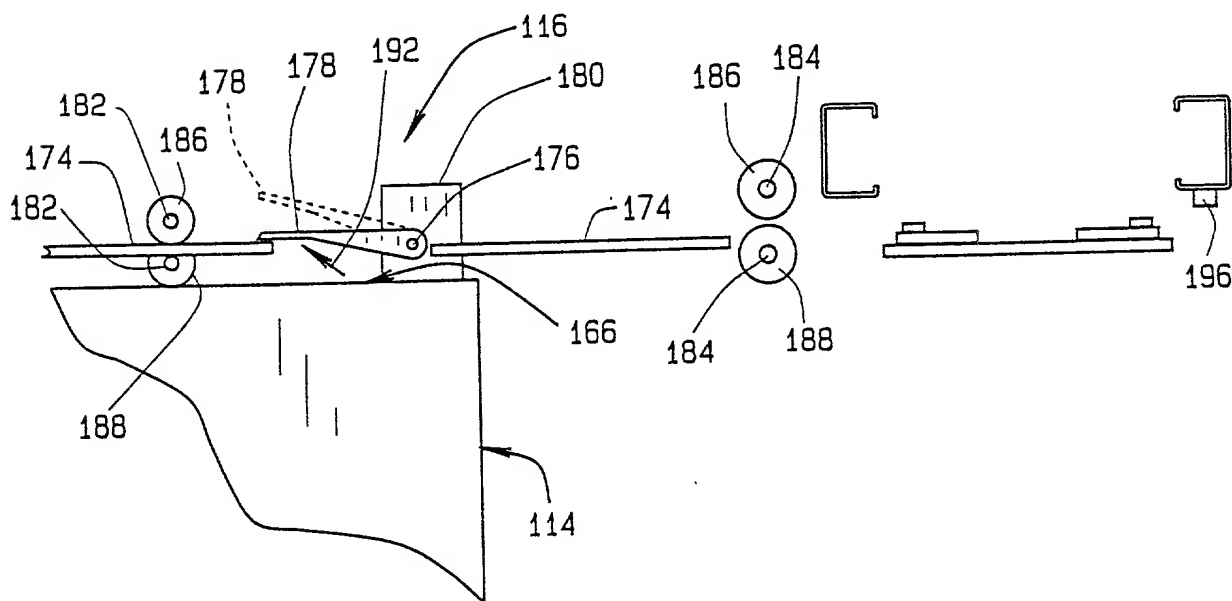


FIG. 20

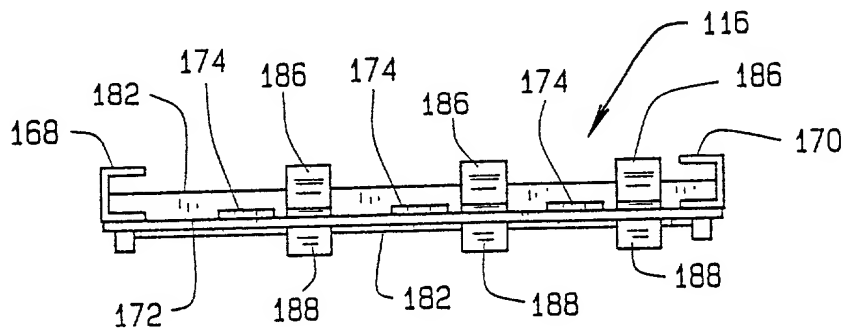


FIG. 21

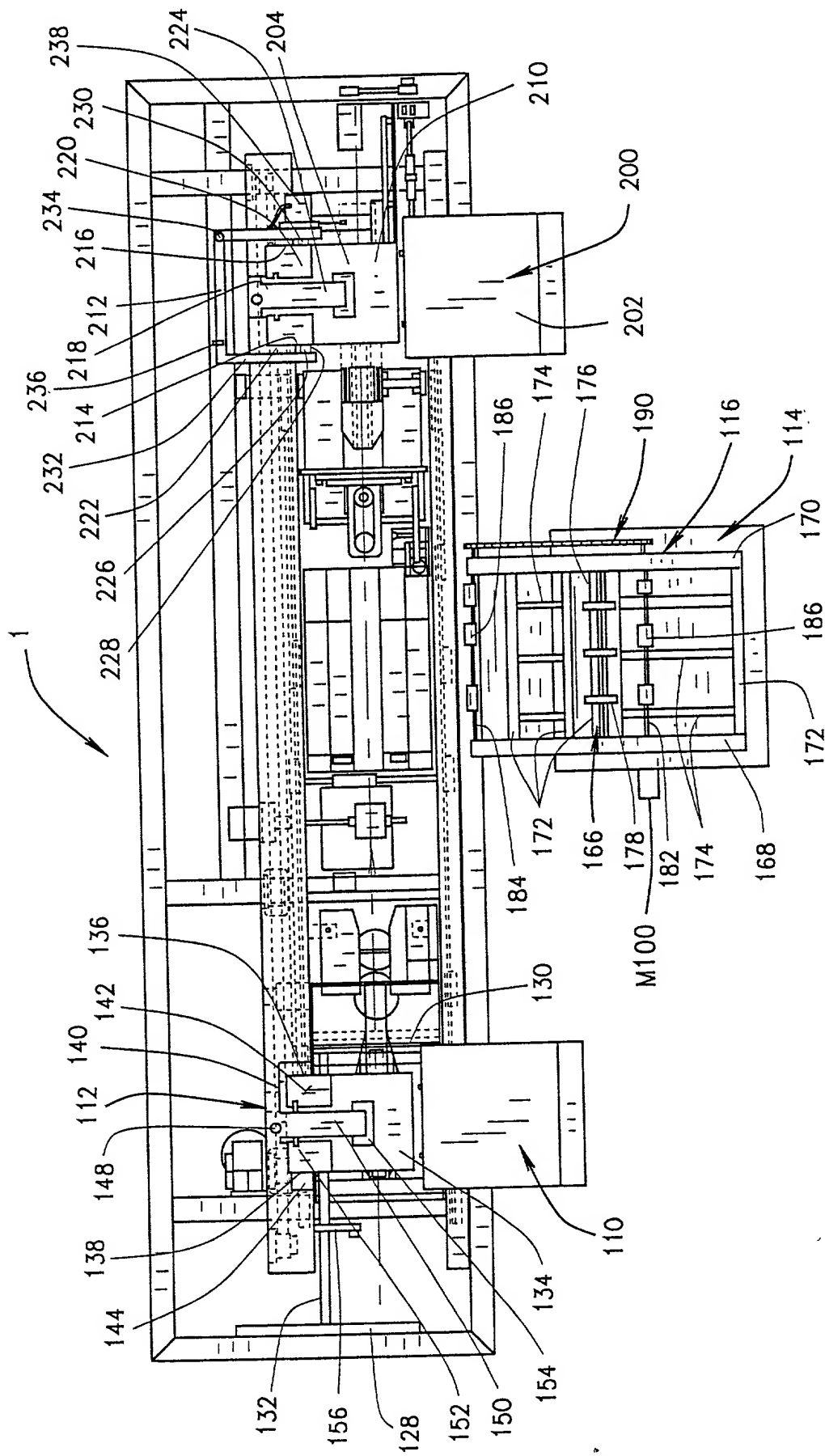


FIG. 22

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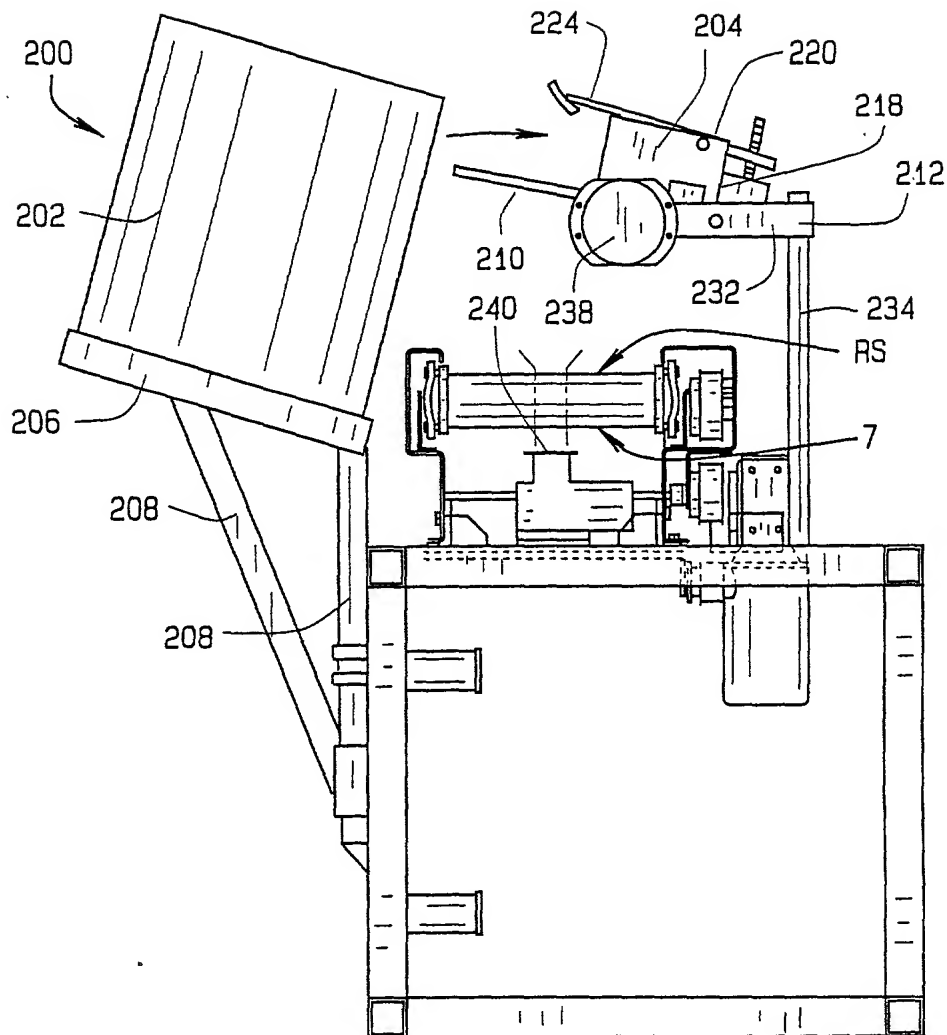


FIG. 23

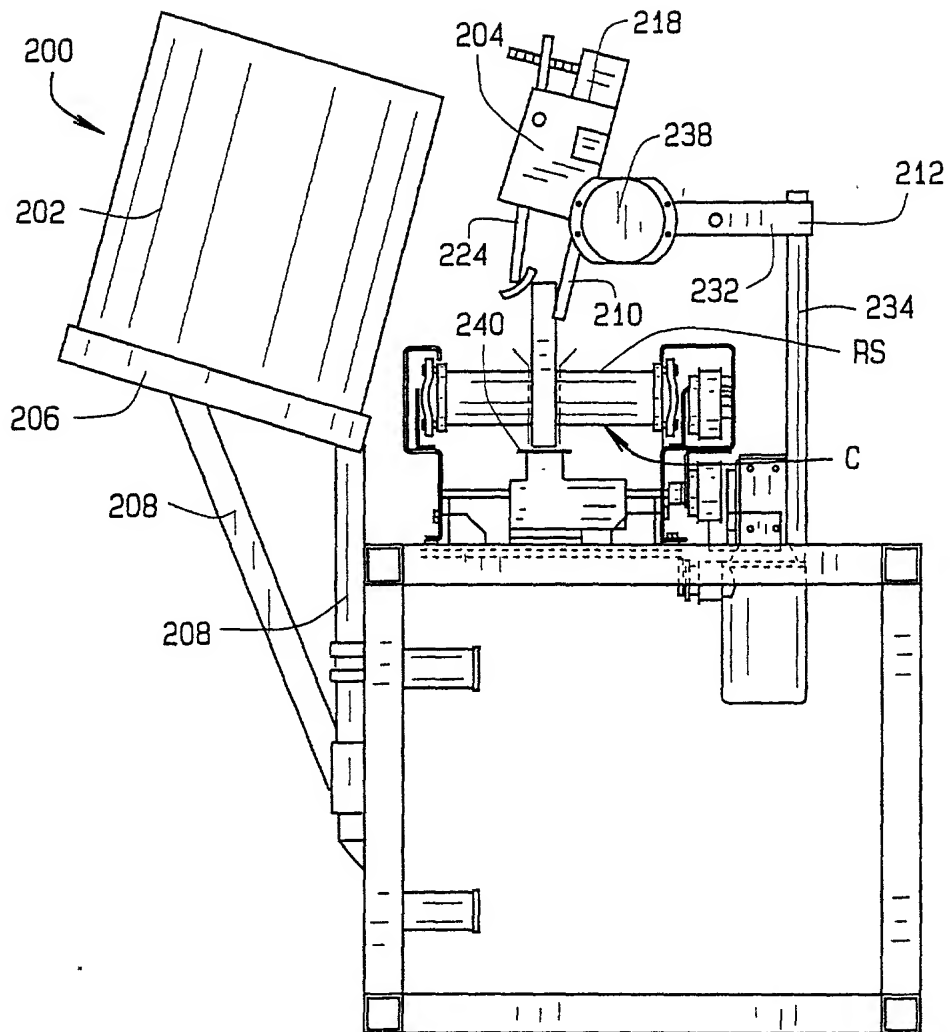


FIG. 24

FIG. 25

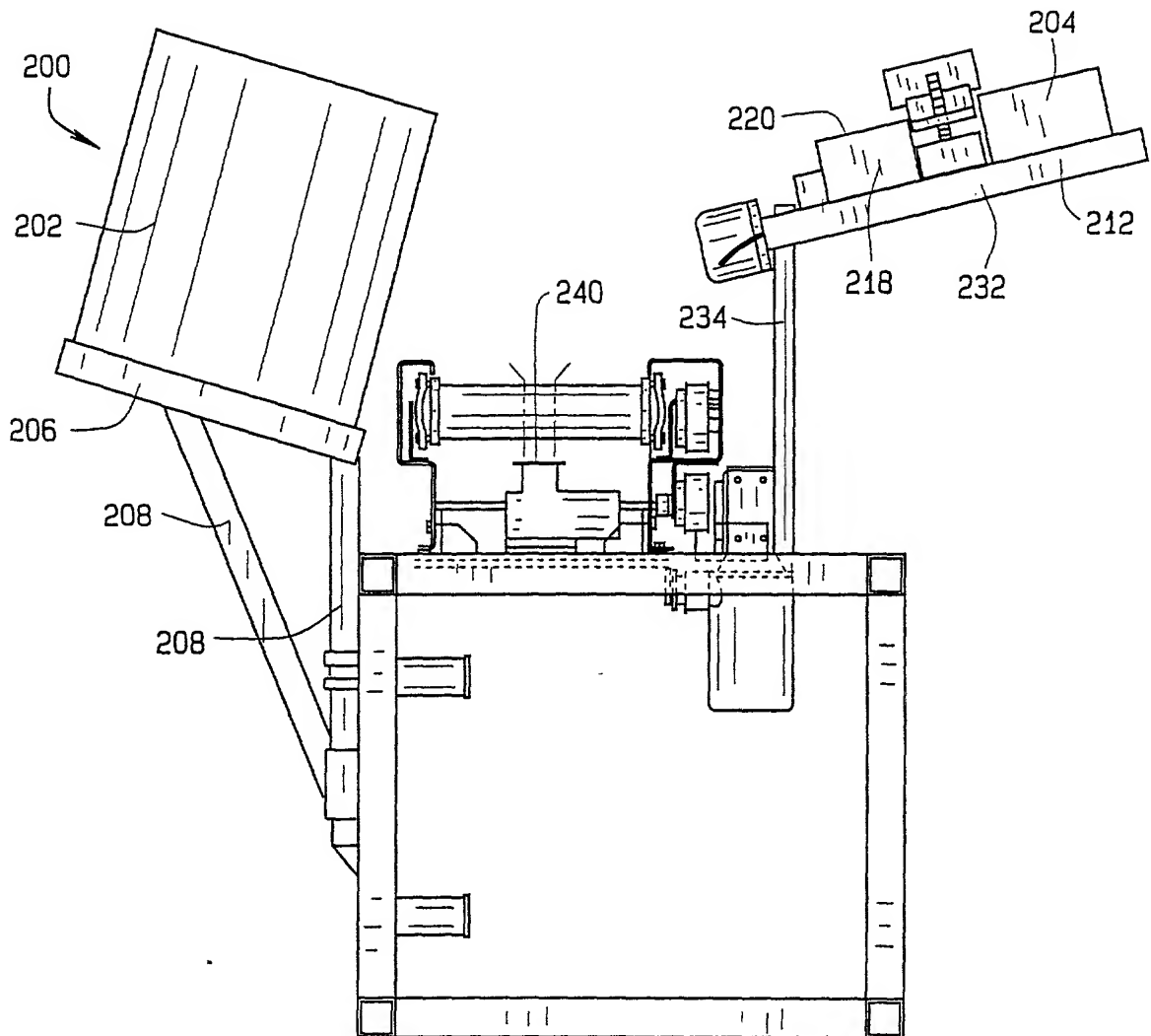


FIG. 25

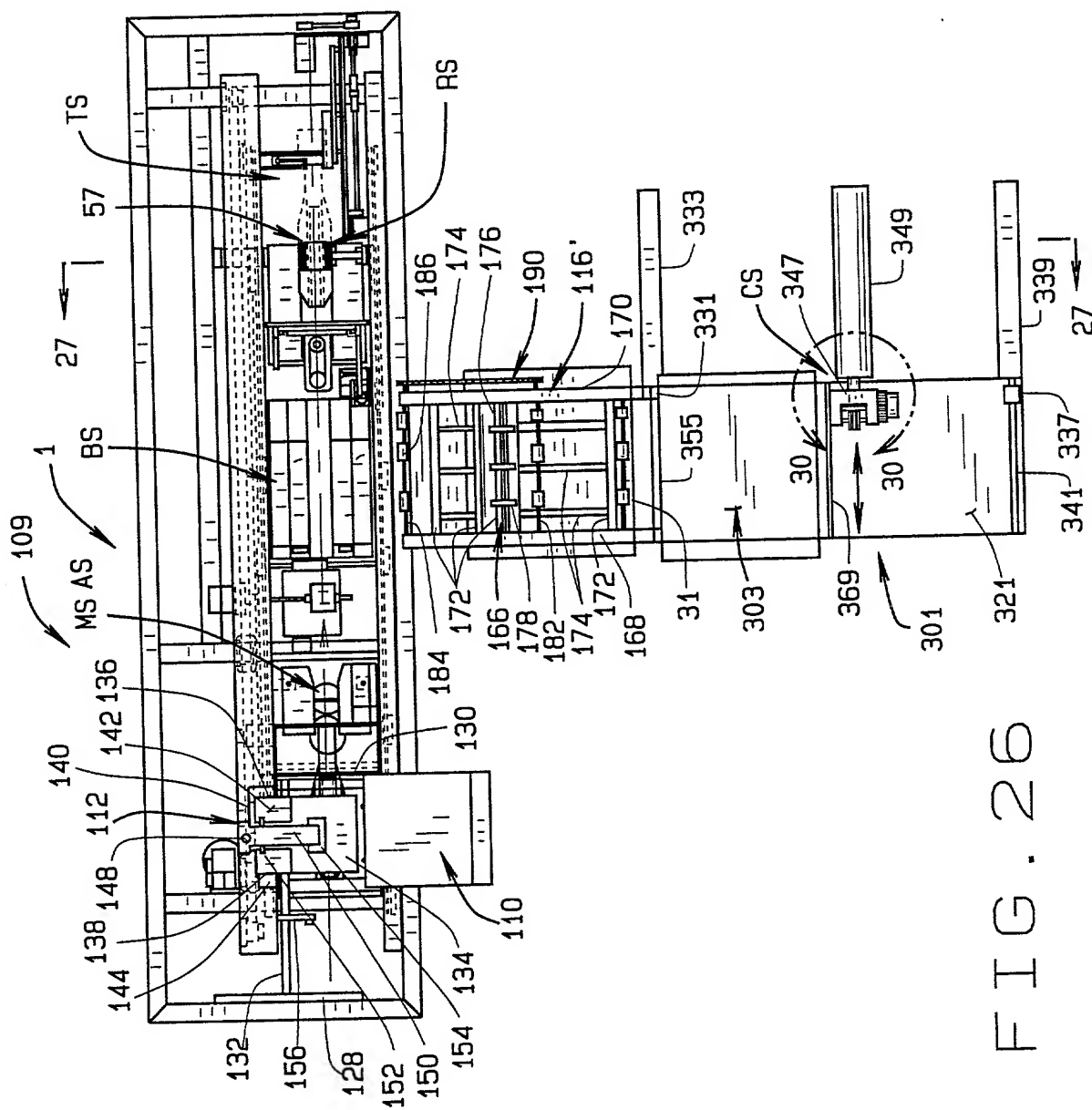


FIG. 26

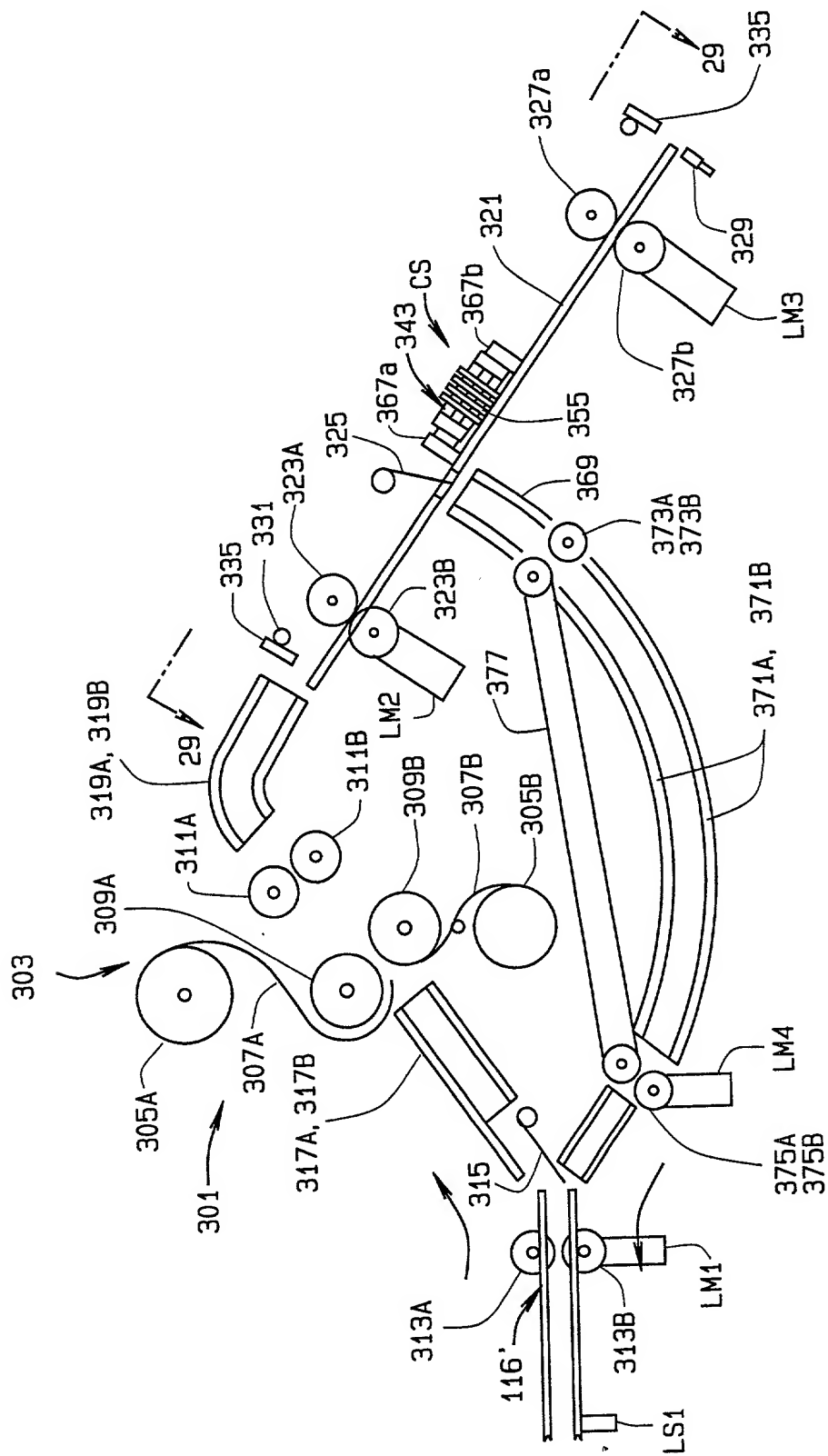


FIG. 28

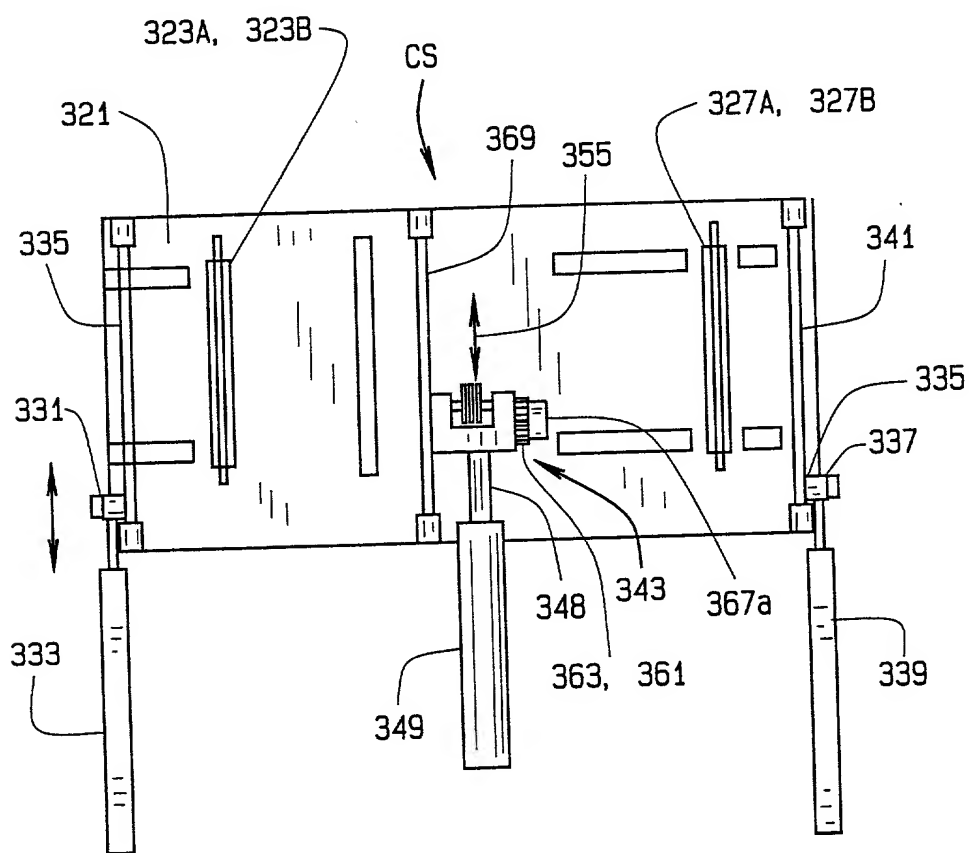


FIG. 29

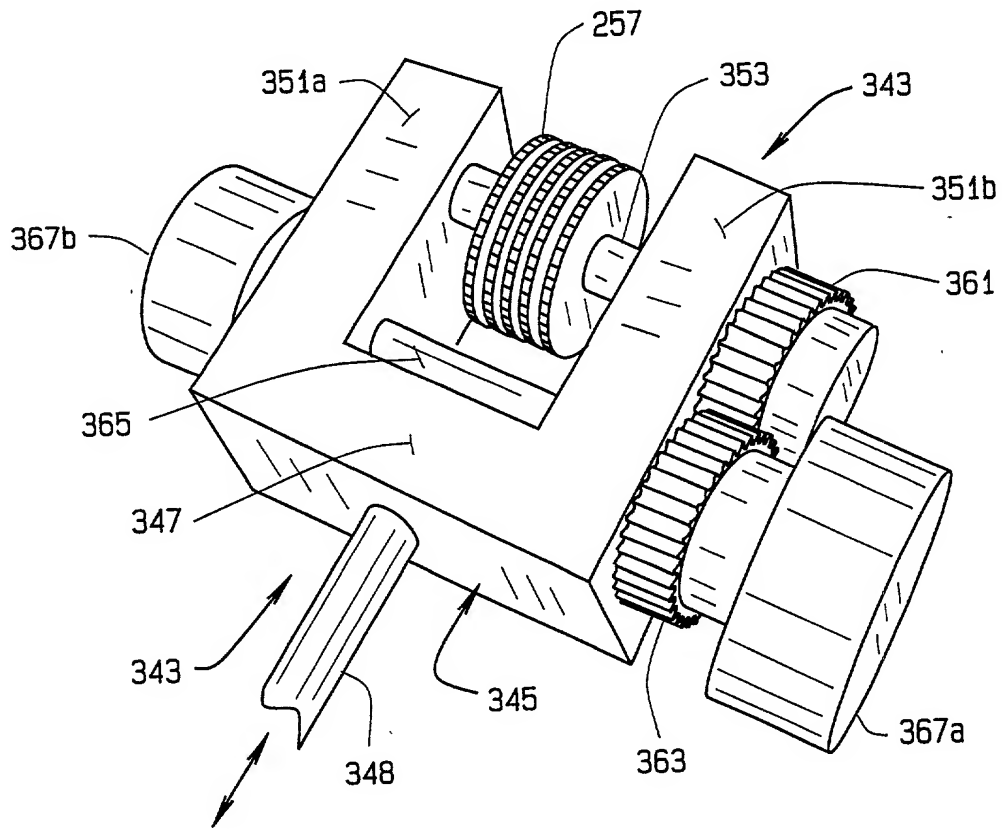


FIG. 30

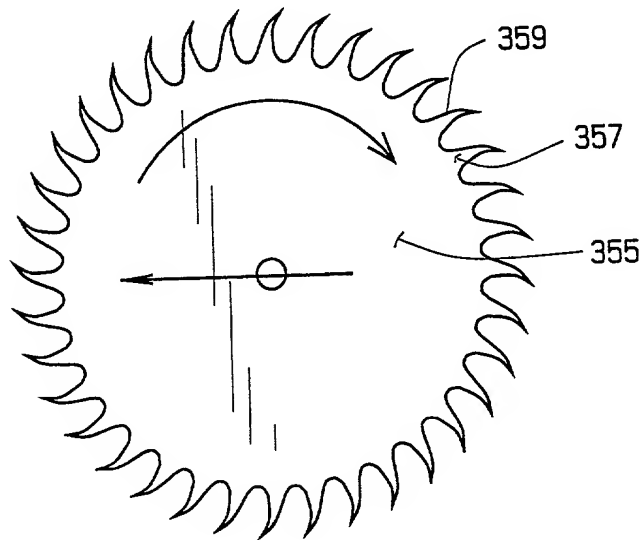


FIG. 31

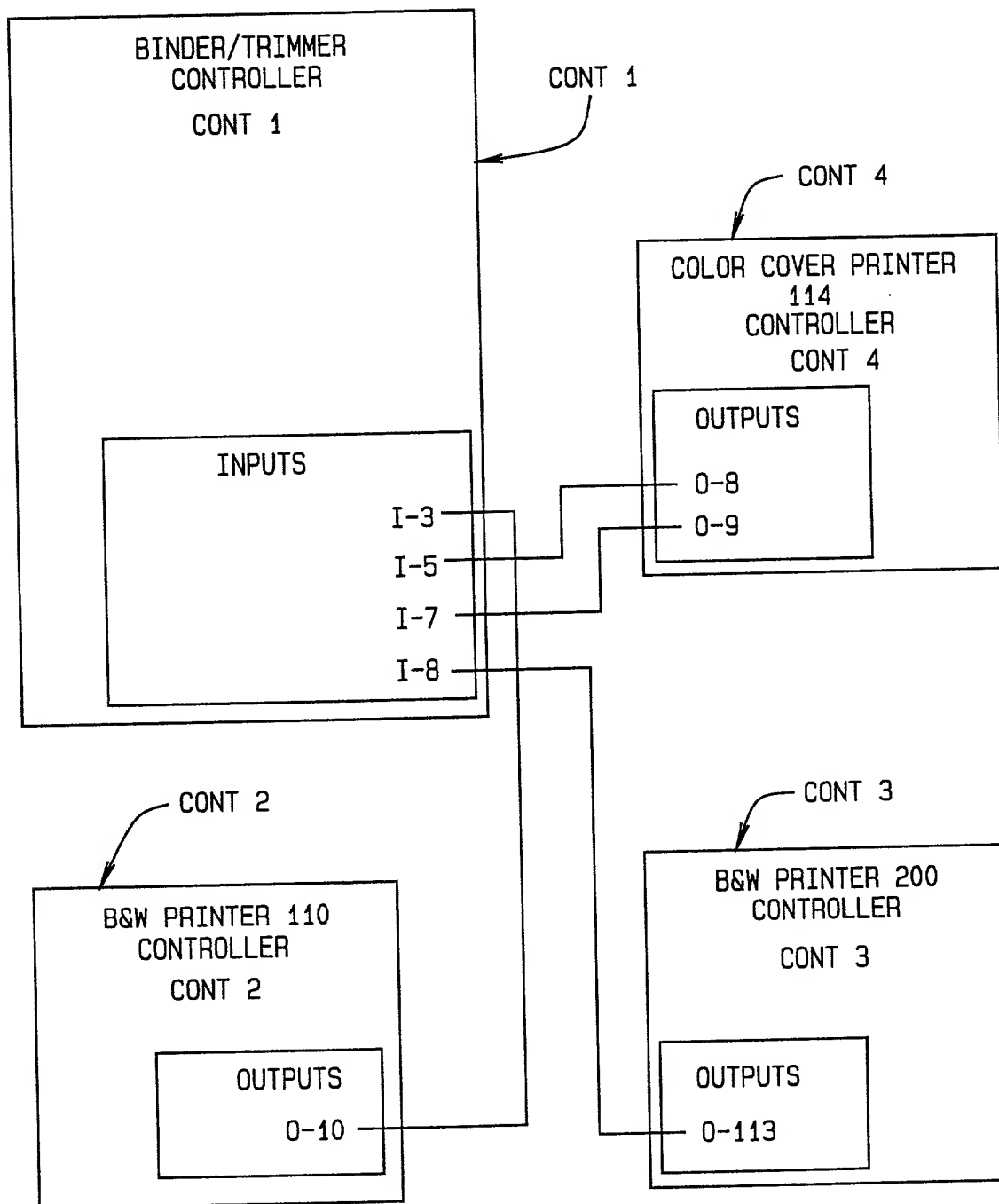


FIG. 32

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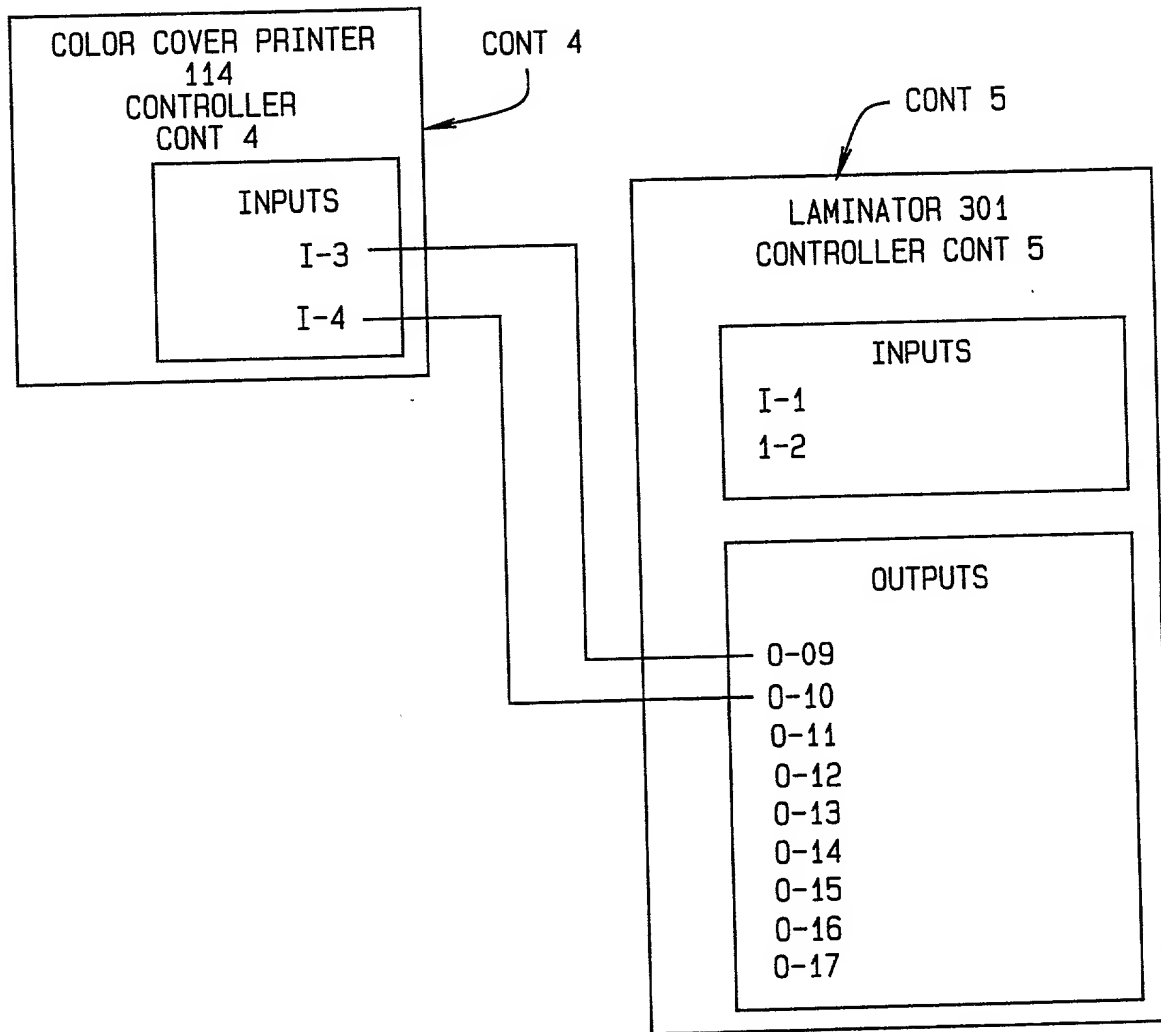


FIG. 33